

ZXMN10A11G

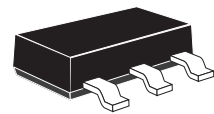
100V N-CHANNEL ENHANCEMENT MODE MOSFET

SUMMARY

$V_{(BR)DSS} = 100V$; $R_{DS(ON)} = 0.6\Omega$ $I_D = 1.8A$

DESCRIPTION

This new generation of TRENCH MOSFETs from Zetex utilises a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



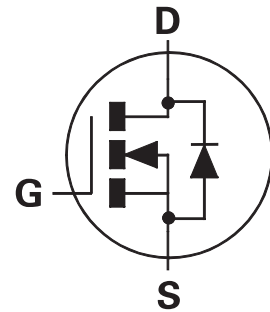
SOT223

FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- SOT223 package

APPLICATIONS

- DC - DC Converters
- Power Management Functions
- Relay and Solenoid driving
- Motor control

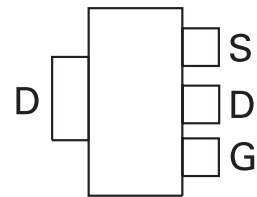


ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXMN10A11GFTA	7"	12mm	1000 units
ZXMN10A11GFTC	13"	12mm	4000 units

DEVICE MARKING

- ZXMN
10A11



Top View

ZXMN10A11G

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DSS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current $V_{GS}=10V$; $T_A=25^{\circ}C$ (b) $V_{GS}=10V$; $T_A=70^{\circ}C$ (b) $V_{GS}=10V$; $T_A=25^{\circ}C$ (a)	I_D	1.8 1.4 1.3	A
Pulsed Drain Current (c)	I_{DM}	5.8	A
Continuous Source Current (Body Diode) (b)	I_S	4.6	A
Pulsed Source Current (Body Diode)(c)	I_{SM}	5.8	A
Power Dissipation at $T_A=25^{\circ}C$ (a) Linear Derating Factor	P_D	2 16	W mW/ $^{\circ}C$
Power Dissipation at $T_A=25^{\circ}C$ (b) Linear Derating Factor	P_D	3.9 31	W mW/ $^{\circ}C$
Operating and Storage Temperature Range	$T_j:T_{stg}$	-55 to +150	$^{\circ}C$

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	$R_{\theta JA}$	62.5	$^{\circ}C/W$
Junction to Ambient (b)	$R_{\theta JA}$	32	$^{\circ}C/W$

NOTES

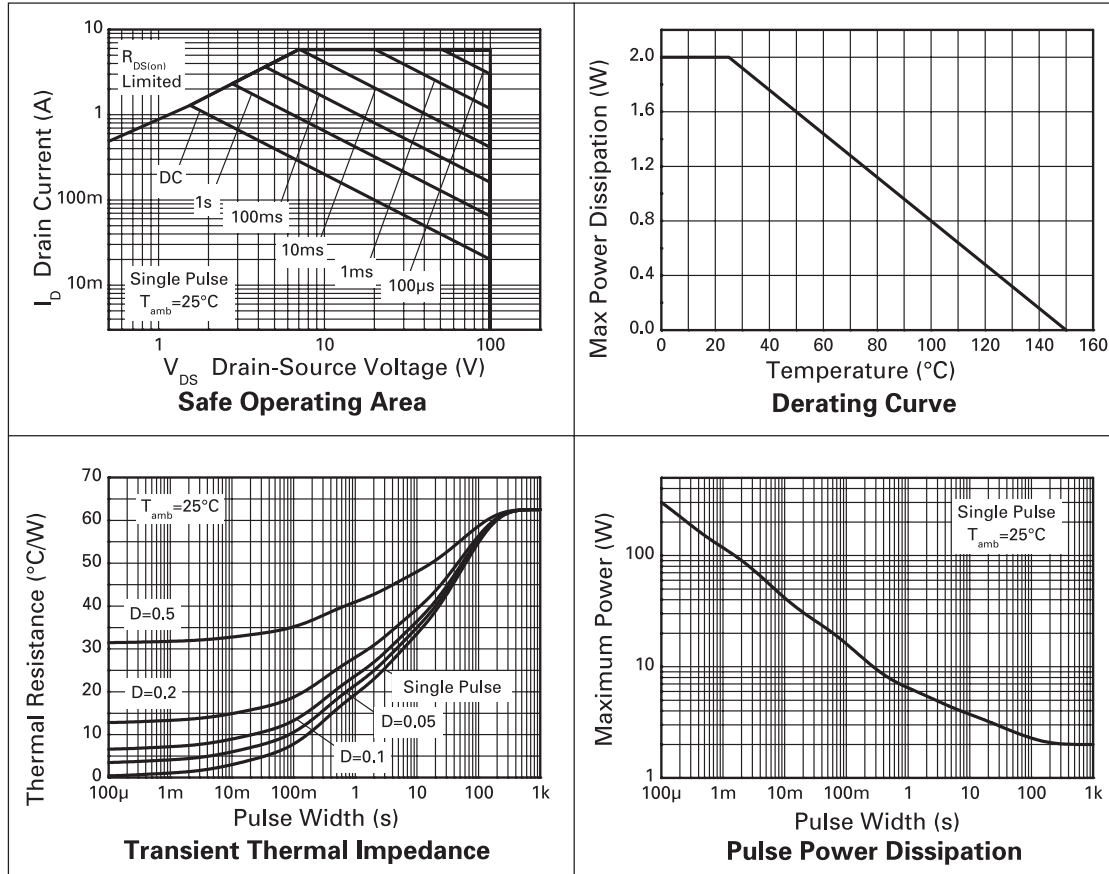
(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

(b) For a device surface mounted on FR4 PCB measured at $t \leq 10$ secs.

(c) Repetitive rating 25mm x 25mm FRA PCB, $D=0.05$ pulse width = 10 μs - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.

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CHARACTERISTICS



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ELECTRICAL CHARACTERISTICS (at TA = 25°C unless otherwise stated)

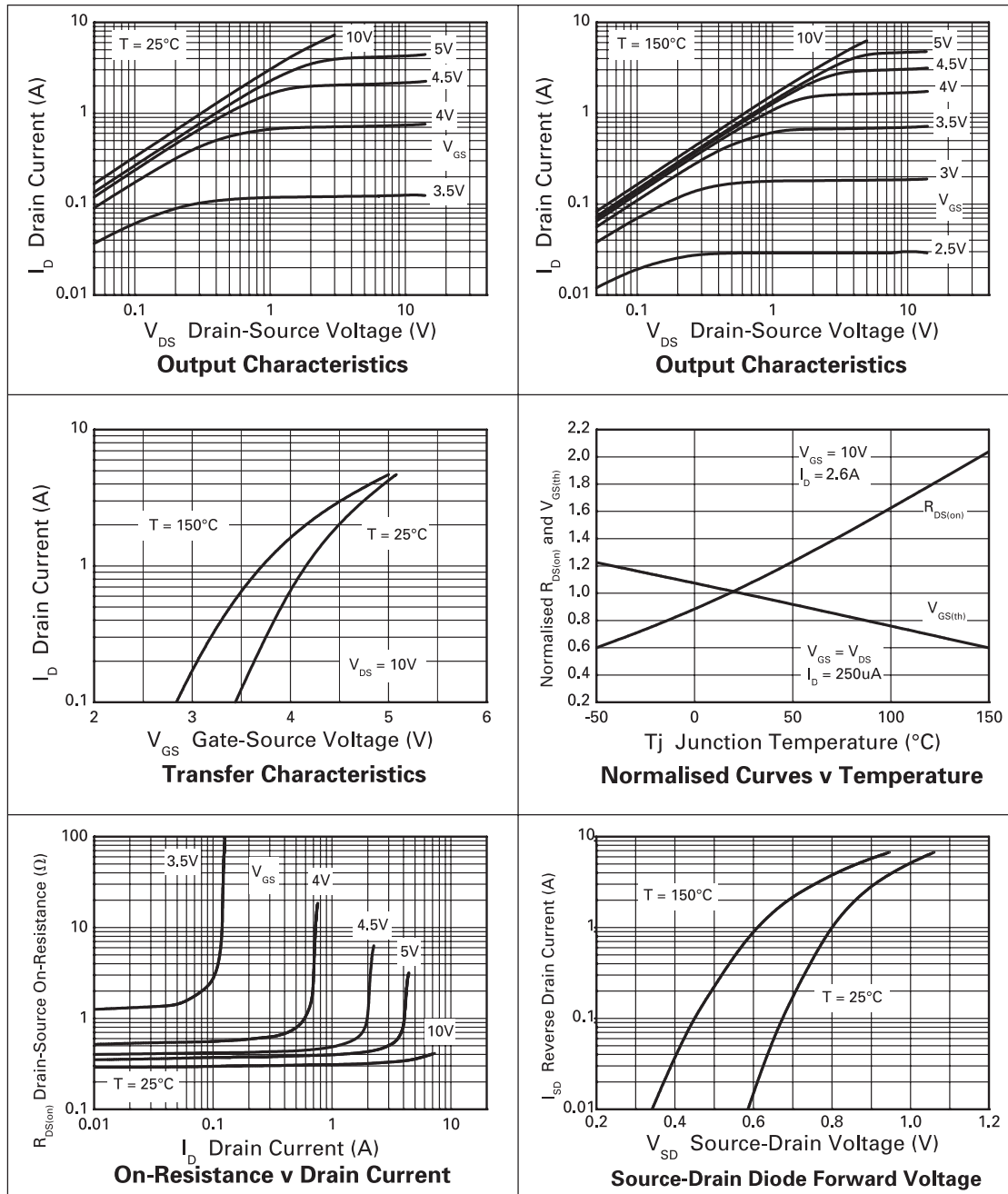
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
STATIC						
Drain-Source Breakdown Voltage	V(BR)DSS	100			V	ID=250μA, VGS=0V
Zero Gate Voltage Drain Current	IDSS			1	μA	VDS=100V, VGS=0V
Gate-Body Leakage	IGSS			100	nA	VGS=±20V, VDS=0V
Gate-Source Threshold Voltage	VGS(th)	2.0		4.0	V	ID=250μA, VDS= VGS
Static Drain-Source On-State Resistance (1)	RDS(on)			0.60 0.70	Ω Ω	VGS=10V, ID=2.6A VGS=6V, ID=1.3A
Forward Transconductance (3)	gfs		3.95		S	VDS=15V,ID=2.6A
DYNAMIC (3)						
Input Capacitance	Ciss		274		pF	VDS=50 V, VGS=0V, f=1MHz
Output Capacitance	Coss		21		pF	
Reverse Transfer Capacitance	Crss		11		pF	
SWITCHING(2) (3)						
Turn-On Delay Time	td(on)		2.7		ns	VDD =50V, ID=1A RG=6.0Ω, VGS=10V
Rise Time	tr		1.7		ns	
Turn-Off Delay Time	td(off)		7.4		ns	
Fall Time	tf		3.5		ns	
Gate Charge	Qg		3		nC	VDS=50V, VGS=5V, ID=2.5A
Total Gate Charge	Qg		5.4		nC	VDS=50V,VGS=10V, ID=2.5A
Gate-Source Charge	Qgs		1.4		nC	
Gate-Drain Charge	Qgd		1.5		nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	VSD		0.85	0.95	V	TJ=25°C, IS=1.85A, VGS=0V
Reverse Recovery Time (3)	trr		26		ns	TJ=25°C, IF=1.0A, di/dt= 100A/μs
Reverse Recovery Charge (3)	Qrr		30		nC	

NOTES

- (1) Measured under pulsed conditions. Width $\leq 300\mu s$. Duty cycle $\leq 2\%$.
(2) Switching characteristics are independent of operating junction temperature.
(3) For design aid only, not subject to production testing.

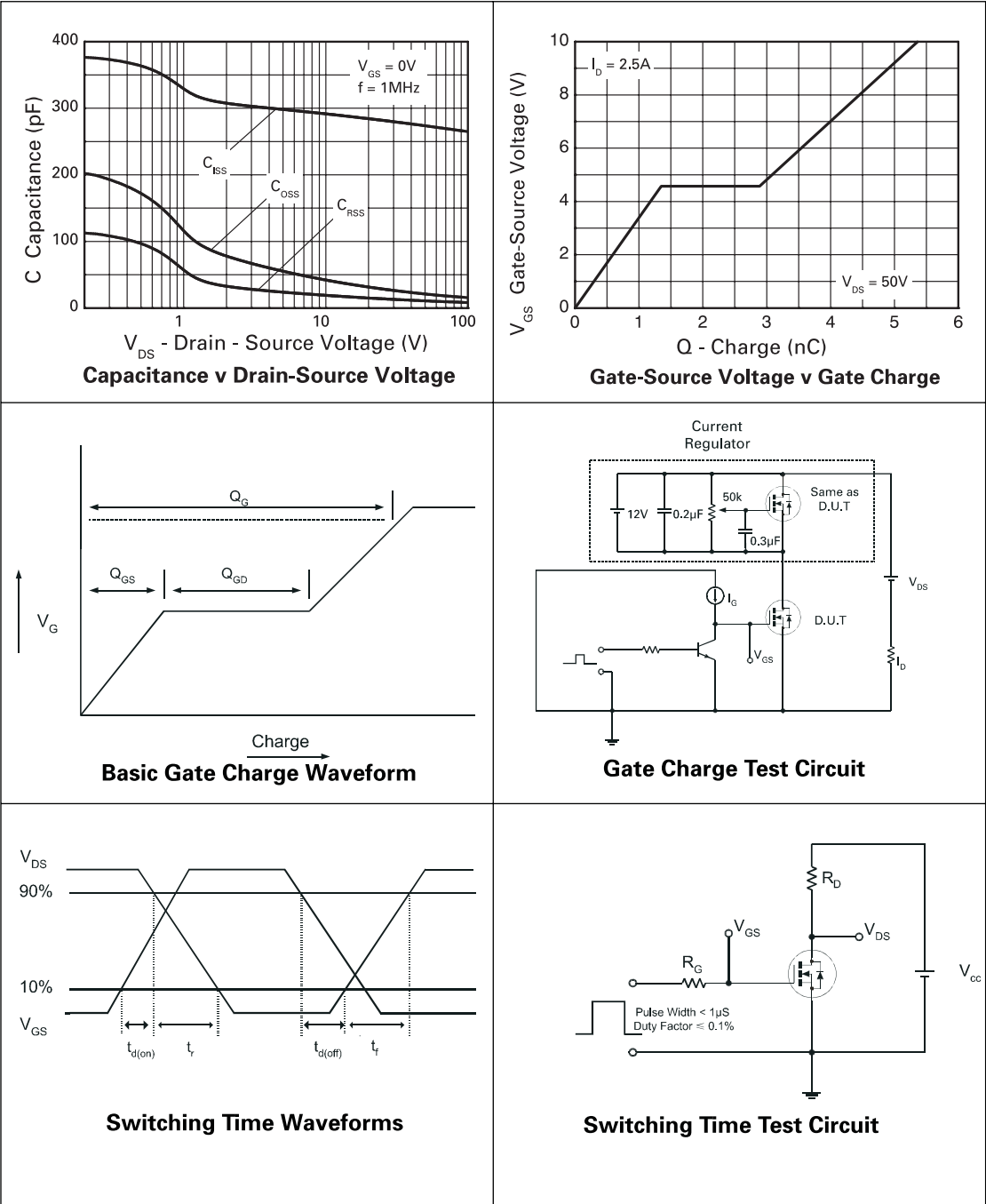
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TYPICAL CHARACTERISTICS



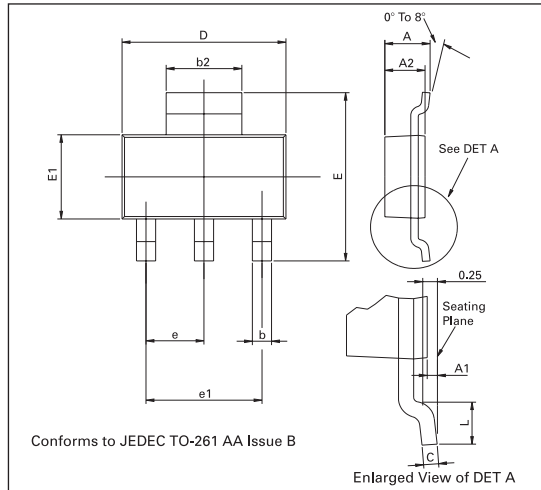
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TYPICAL CHARACTERISTICS



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PACKAGE OUTLINE



PACKAGE DIMENSIONS

DIM	MILLIMETRES	
	MIN	MAX
A	—	1.80
A1	0.02	0.10
A2	1.55	1.65
b	0.66	0.84
b2	2.90	3.10
C	0.23	0.33
D	6.30	6.70
e	2.30 BASIC	
e1	4.60 BASIC	
E	6.70	7.30
E1	3.30	3.70
L	0.90	—

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Zetex plc
Fields New Road
Chadderton
Oldham, OL9 8NP
United Kingdom
Telephone (44) 161 622 4422
Fax: (44) 161 622 4420

Zetex GmbH
Streitfeldstraße 19
D-81673 München
Germany
Telefon: (49) 89 45 49 49 0
Fax: (49) 89 45 49 49 49

Zetex Inc
700 Veterans Memorial Hwy
Hauppauge, NY11788
USA
Telephone: (631) 360 2222
Fax: (631) 360 8222

Zetex (Asia) Ltd
3701-04 Metroplaza, Tower 1
Hing Fong Road
Kwai Fong
Hong Kong
Telephone: (852) 26100 611
Fax: (852) 24250 494

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